

## **isc** Silicon NPN Power Transistor

# 2SD1712

### DESCRIPTION

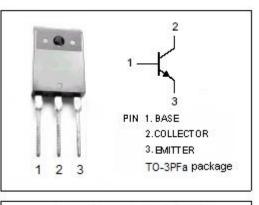
- Collector-Emitter Breakdown Voltage-: V<sub>(BR)CEO</sub>= 100V(Min)
- Good Linearity of h<sub>FE</sub>
- Wide Area of Safe Operation
- Complement to Type 2SB1157
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

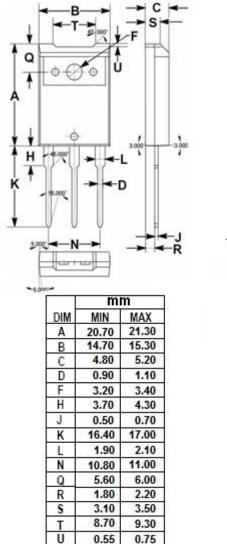
### APPLICATIONS

• Designed for high power amplifier applications.

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	100	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	100	V	
V <sub>EBO</sub>	Emitter-Base Voltage	5	V	
lc	Collector Current-Continuous	5	A	
I <sub>CP</sub>	Collector Current-Pulse	8	A	
Pc	Collector Power Dissipation @ $T_C$ =25°C	60	w	
	Collector Power Dissipation @ T <sub>a</sub> =25℃	3		
TJ	Junction Temperature	150	°C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	Ĉ	

### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)







## **isc Silicon NPN Power Transistor**

# 2SD1712

### **ELECTRICAL CHARACTERISTICS**

### $T_{\text{C}}\text{=}25^{\circ}\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.3A			2.0	V
V <sub>BE(on)</sub>	Base -Emitter On Voltage	I <sub>C</sub> = 3A; V <sub>CE</sub> = 5V			1.8	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 100V; I <sub>E</sub> = 0			50	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 3V; I <sub>C</sub> = 0			50	μA
h <sub>FE-1</sub>	DC Current Gain	Ic= 20mA; Vce= 5V	20			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V	60		200	
h <sub>FE-3</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 5V	20			
Сов	Collector Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f= 1MHz		70		pF
fT	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 5V		20		MHz

### h<sub>FE-2</sub> Classifications

Q	S	Р
60-120	80-160	100-200

### **NOTICE:**

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.

isc website: www.iscsemi.com